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Kind regards,

Team Nexperia



# BSH111BK

55 V, N-channel Trench MOSFET

26 November 2014

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 3 kV HBM

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ °C}$	-	-	55	V
$V_{GS}$	gate-source voltage		-10	-	10	V
$I_D$	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	210	mA
		$V_{GS} = 4.5\text{ V}; T_{sp} = 25\text{ °C}$		-	335	mA
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 200\text{ mA}; T_j = 25\text{ °C}$	-	2.3	4	$\Omega$

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain  $1\text{ cm}^2$ .

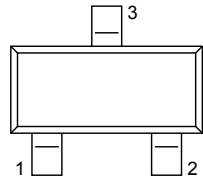
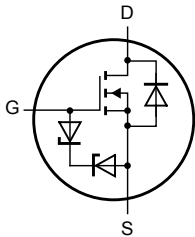


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-236AB (SOT23)</p>	 <p>017aaa255</p>
2	S	source		
3	D	drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BSH111BK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BSH111BK	%4T

[1] % = placeholder for manufacturing site code

## 8. Limiting values

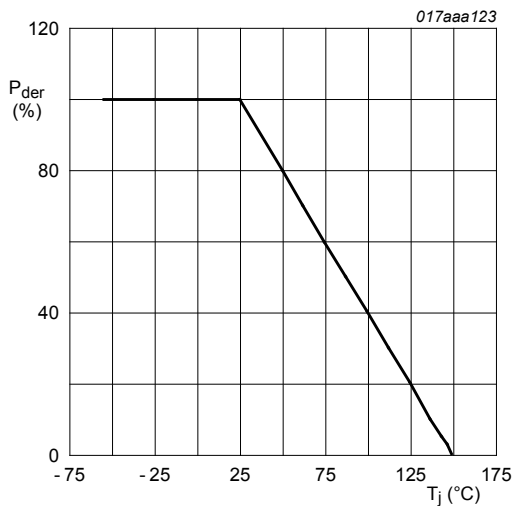
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	55	V
V <sub>GS</sub>	gate-source voltage			-10	10	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	210	mA
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	130	mA
		V <sub>GS</sub> = 4.5 V; T <sub>sp</sub> = 25 °C		-	335	mA
I <sub>DM</sub>	peak drain current	T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs		-	0.85	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	302	mW
			[1]	-	364	mW
		T <sub>sp</sub> = 25 °C		-	1449	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
<b>Source-drain diode</b>						
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	200	mA

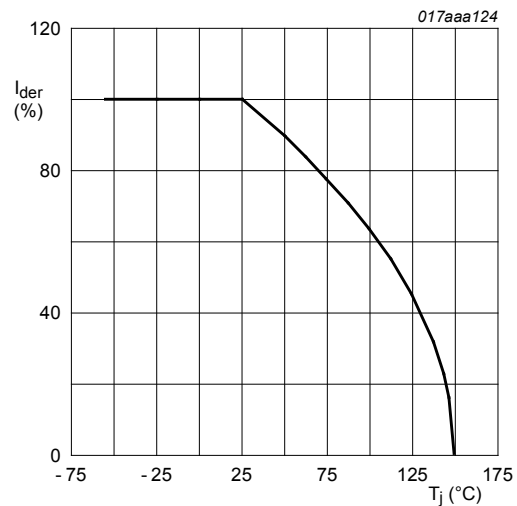
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



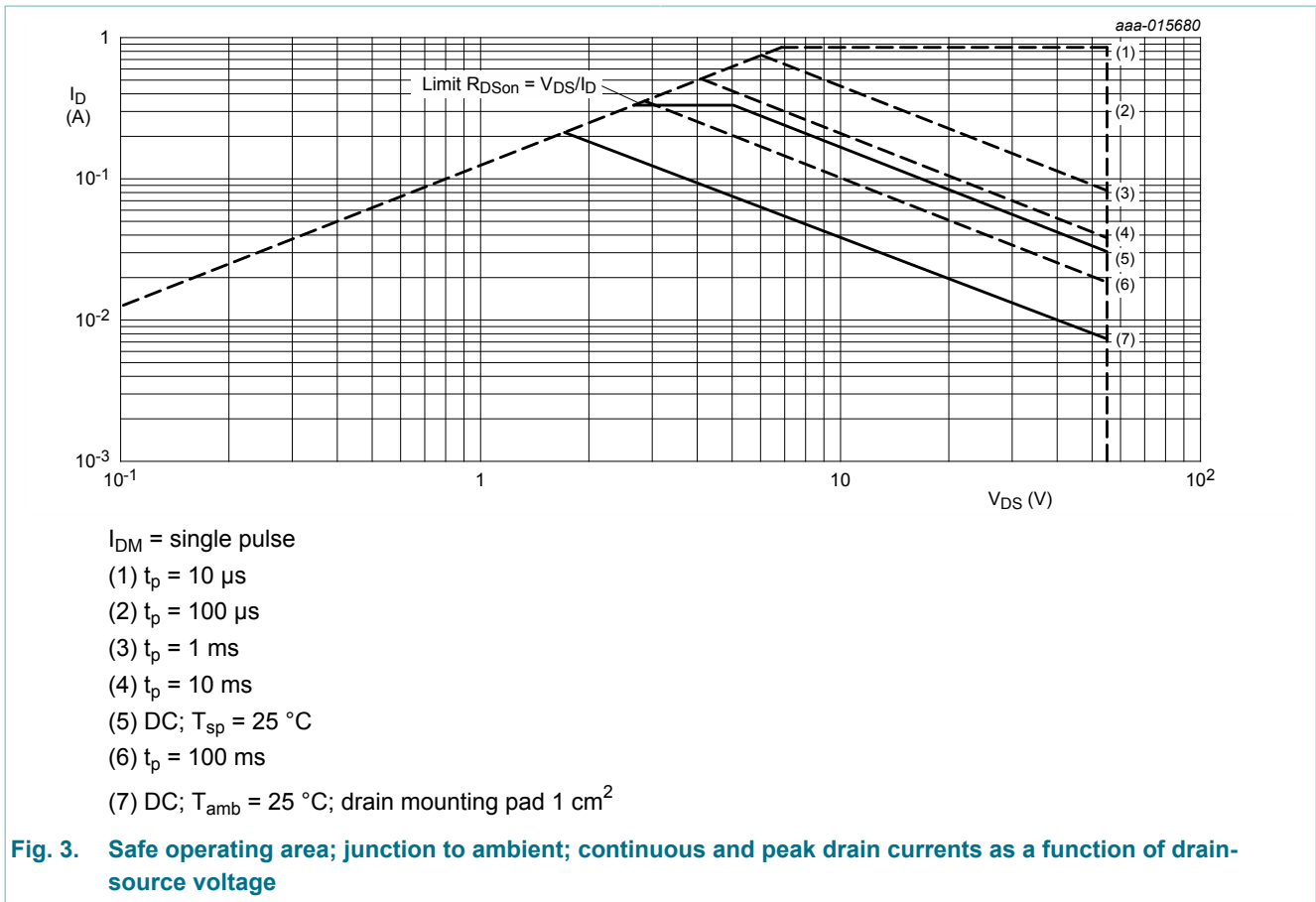
**Fig. 1. Normalized total power dissipation as a function of junction temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \%$$



**Fig. 2. Normalized continuous drain current as a function of junction temperature**

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$



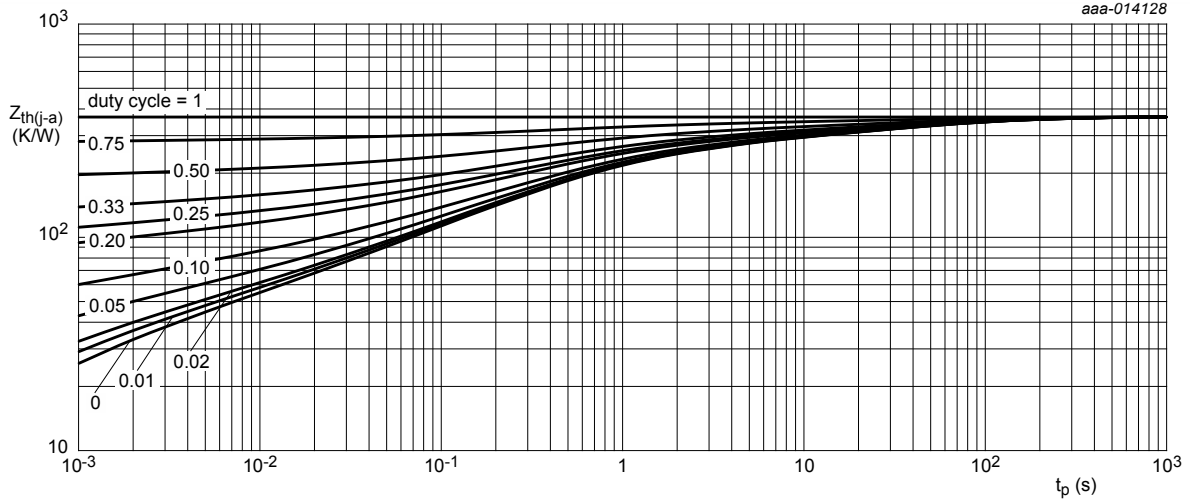
## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	351	404	K/W
			[2]	-	271	311	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	65	75	K/W

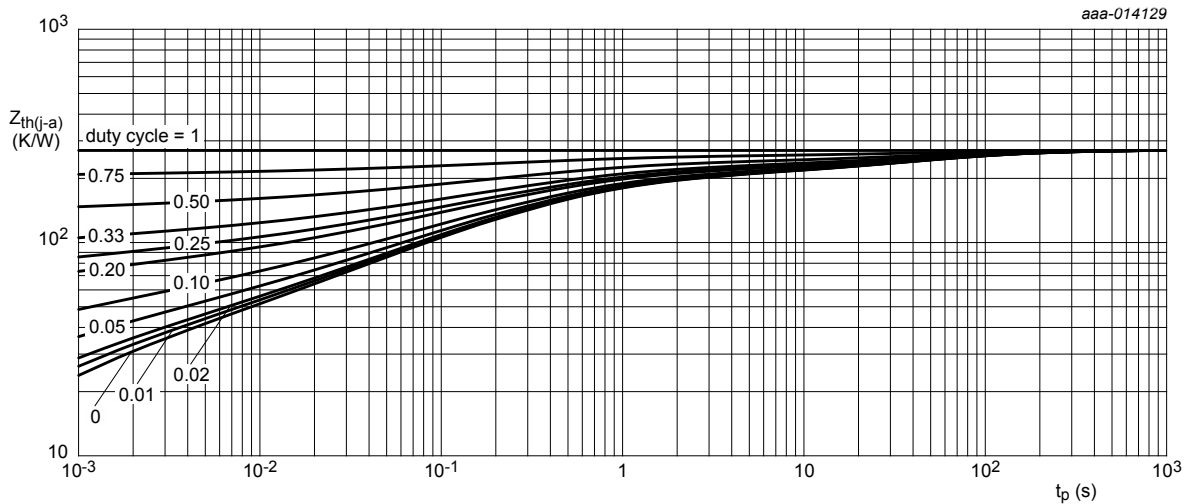
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain  $1 \text{ cm}^2$ .



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



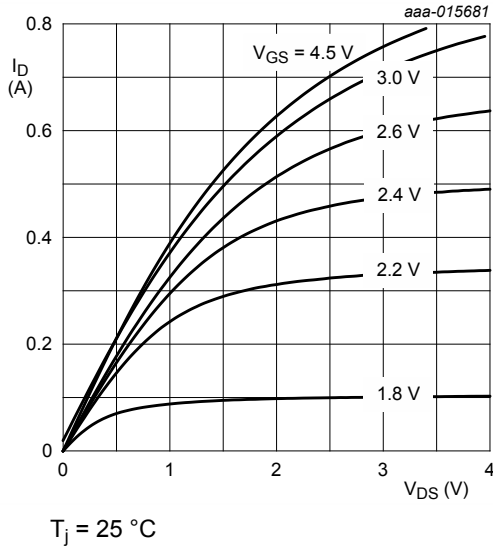
FR4 PCB, mounting pad for drain 1 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

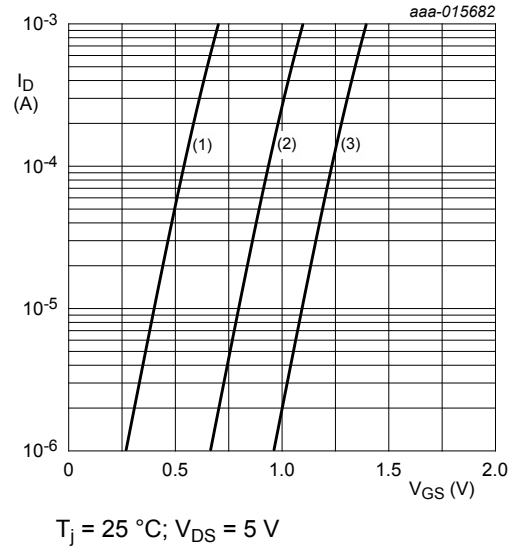
## 10. Characteristics

Table 7. Characteristics

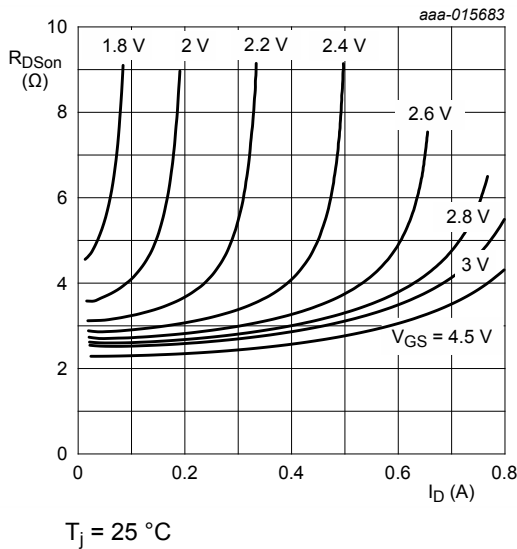
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	55	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	0.6	1	1.3	V
$I_{DSS}$	drain leakage current	$V_{DS} = 55 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	5	$\mu A$
		$V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-5	$\mu A$
		$V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	0.3	$\mu A$
		$V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-0.3	$\mu A$
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 V; I_D = 200 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	2.3	4	$\Omega$
		$V_{GS} = 4.5 V; I_D = 200 \text{ mA}; T_j = 150 \text{ }^\circ C$	-	4.7	8.1	$\Omega$
		$V_{GS} = 2.5 V; I_D = 75 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	2.7	5	$\Omega$
		$V_{GS} = 1.8 V; I_D = 30 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	4.8	-	$\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 10 V; I_D = 200 \text{ mA}; T_j = 25 \text{ }^\circ C$	-	0.64	-	S
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 30 V; I_D = 200 \text{ mA}; V_{GS} = 4.5 V; T_j = 25 \text{ }^\circ C$	-	0.5	-	nC
$Q_{GS}$	gate-source charge		-	0.08	-	nC
$Q_{GD}$	gate-drain charge		-	0.16	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 30 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	19.1	30	pF
$C_{oss}$	output capacitance		-	2.7	10	pF
$C_{riss}$	reverse transfer capacitance		-	1.5	7	pF
$t_{d(on)}$	turn-on delay time		$V_{DS} = 30 V; I_D = 200 \text{ mA}; V_{GS} = 4.5 V; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ }^\circ C$	-	8.3	12
$t_r$	rise time	-		8.4	-	ns
$t_{d(off)}$	turn-off delay time	-		12.6	16	ns
$t_f$	fall time	-		4.8	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 200 \text{ mA}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.86	1.2	V



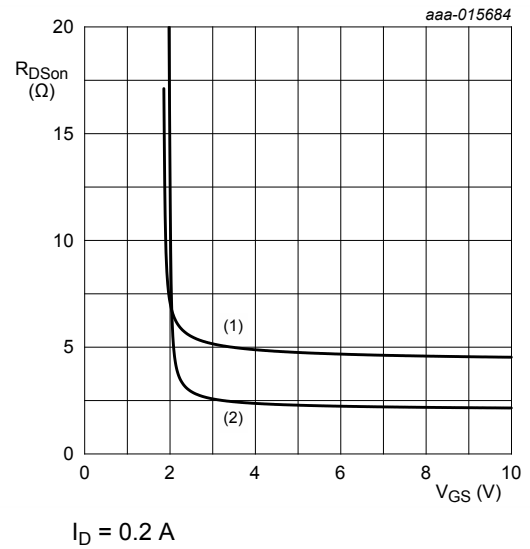
**Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values**



**Fig. 7. Sub-threshold drain current as a function of gate-source voltage**  
 $T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$   
 (1) minimum values  
 (2) typical values  
 (3) maximum values

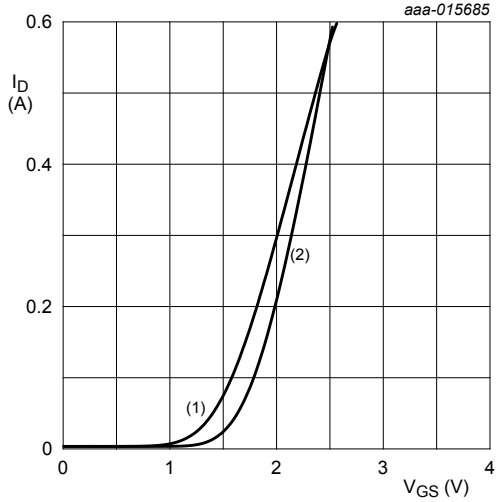


**Fig. 8. Drain-source on-state resistance as a function of drain current; typical values**



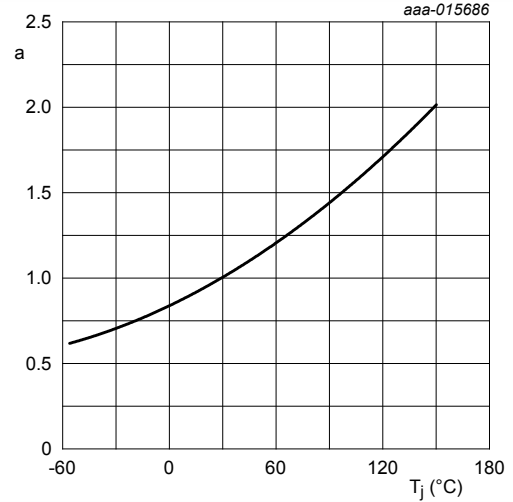
**Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values**  
 $I_D = 0.2\text{ A}$   
 (1)  $T_j = 150\text{ }^\circ\text{C}$   
 (2)  $T_j = 25\text{ }^\circ\text{C}$





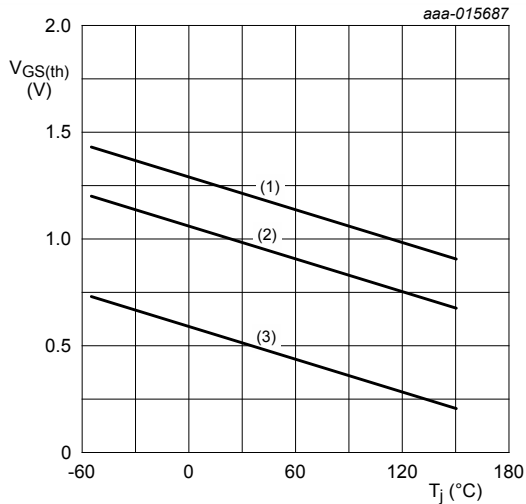
$V_{DS} > I_D \times R_{DS(on)}$   
 (1)  $T_j = 25\text{ °C}$   
 (2)  $T_j = 150\text{ °C}$

**Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



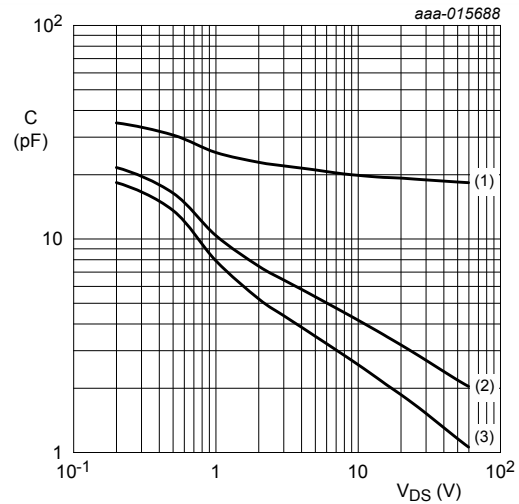
**Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values**

$$a = \frac{R_{DS(on)}}{R_{DS(on)@25^\circ\text{C}}}$$



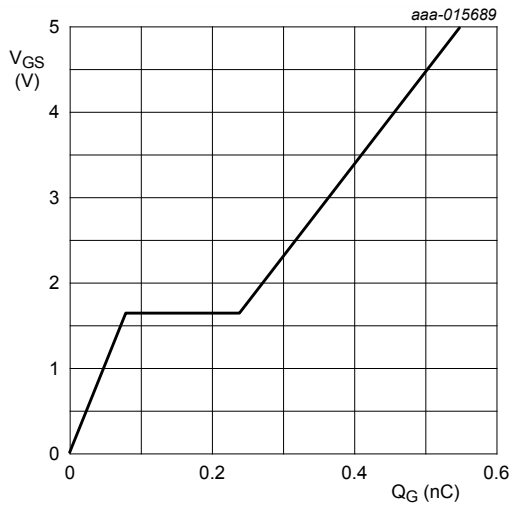
$I_D = 0.25\text{ mA}; V_{DS} = V_{GS}$   
 (1) maximum values  
 (2) typical values  
 (3) minimum values

**Fig. 12. Gate-source threshold voltage as a function of junction temperature**



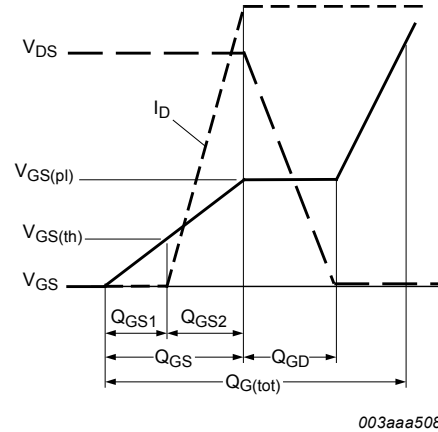
$f = 1\text{ MHz}; V_{GS} = 0\text{ V}$   
 (1)  $C_{iss}$   
 (2)  $C_{oss}$   
 (3)  $C_{rss}$

**Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

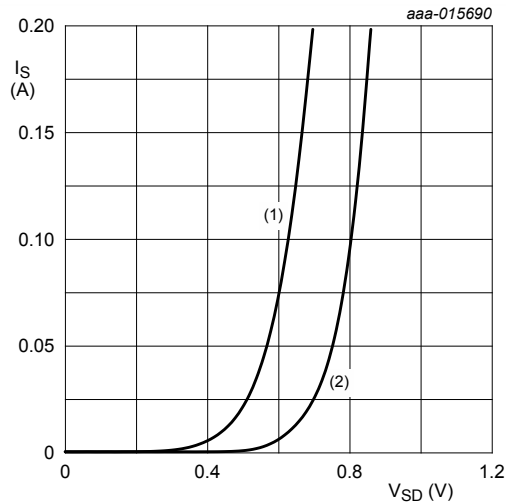


$I_D = 0.2 \text{ A}; V_{DS} = 30 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig. 14. Gate-source voltage as a function of gate charge; typical values**



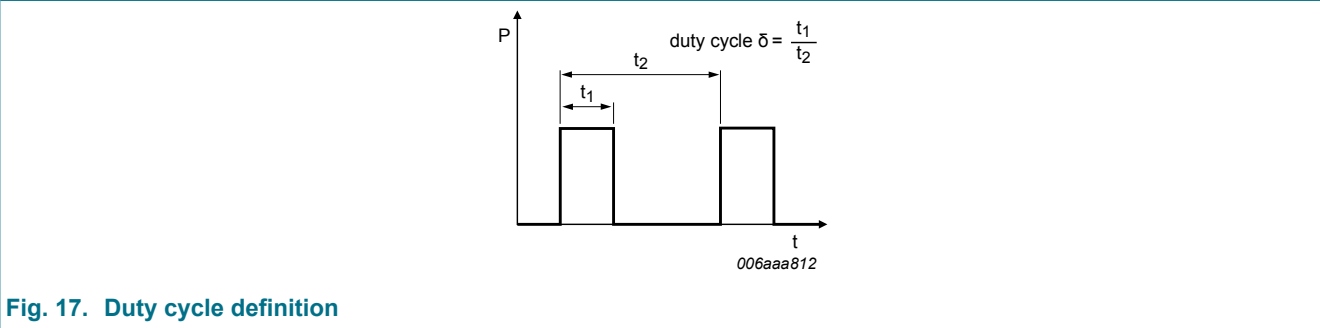
**Fig. 15. MOSFET transistor: Gate charge waveform definitions**



$V_{GS} = 0 \text{ V}$   
 (1)  $T_j = 150 \text{ }^\circ\text{C}$   
 (2)  $T_j = 25 \text{ }^\circ\text{C}$

**Fig. 16. Source current as a function of source-drain voltage; typical values**

**11. Test information**



**Fig. 17. Duty cycle definition**

## 12. Package outline

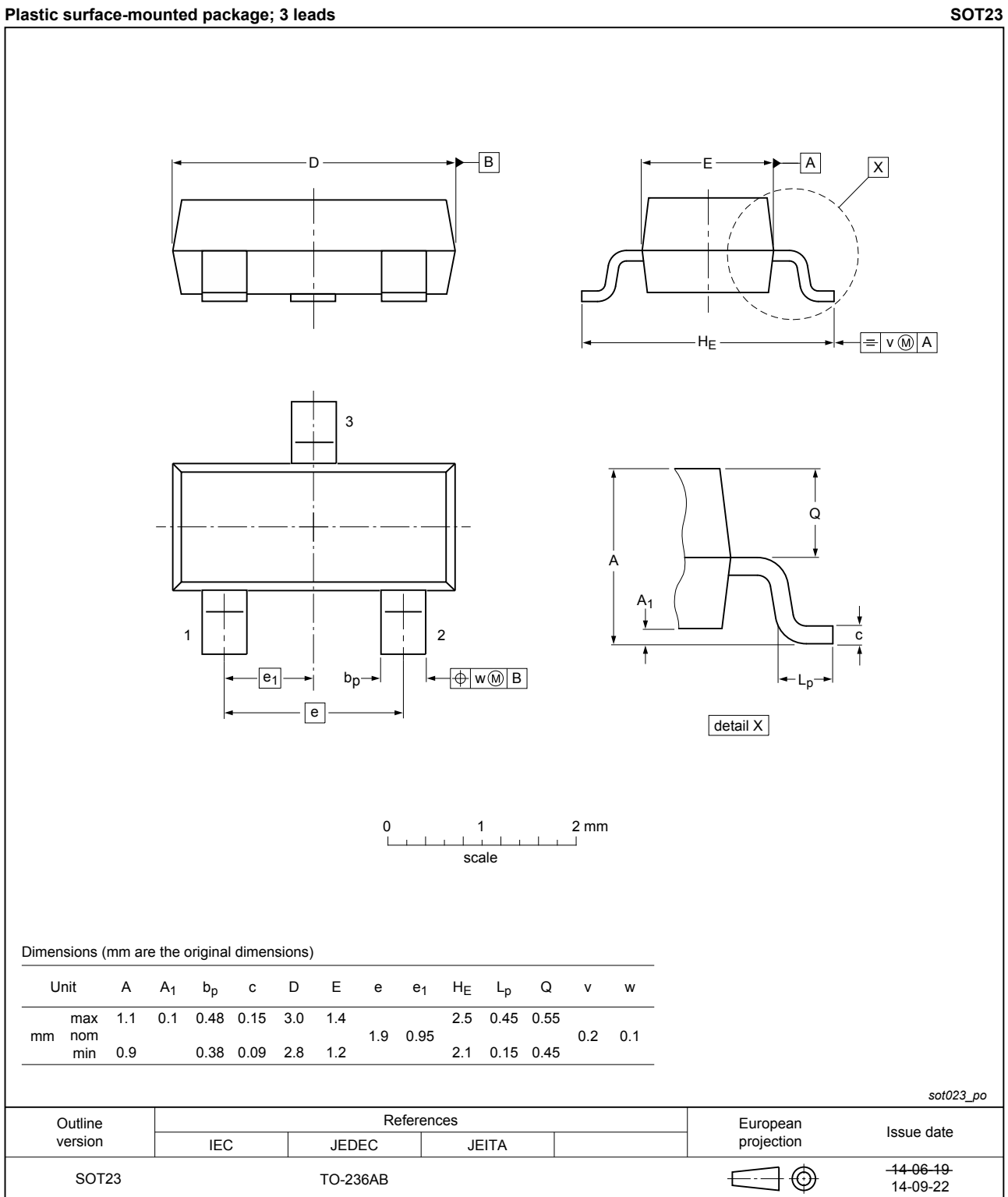
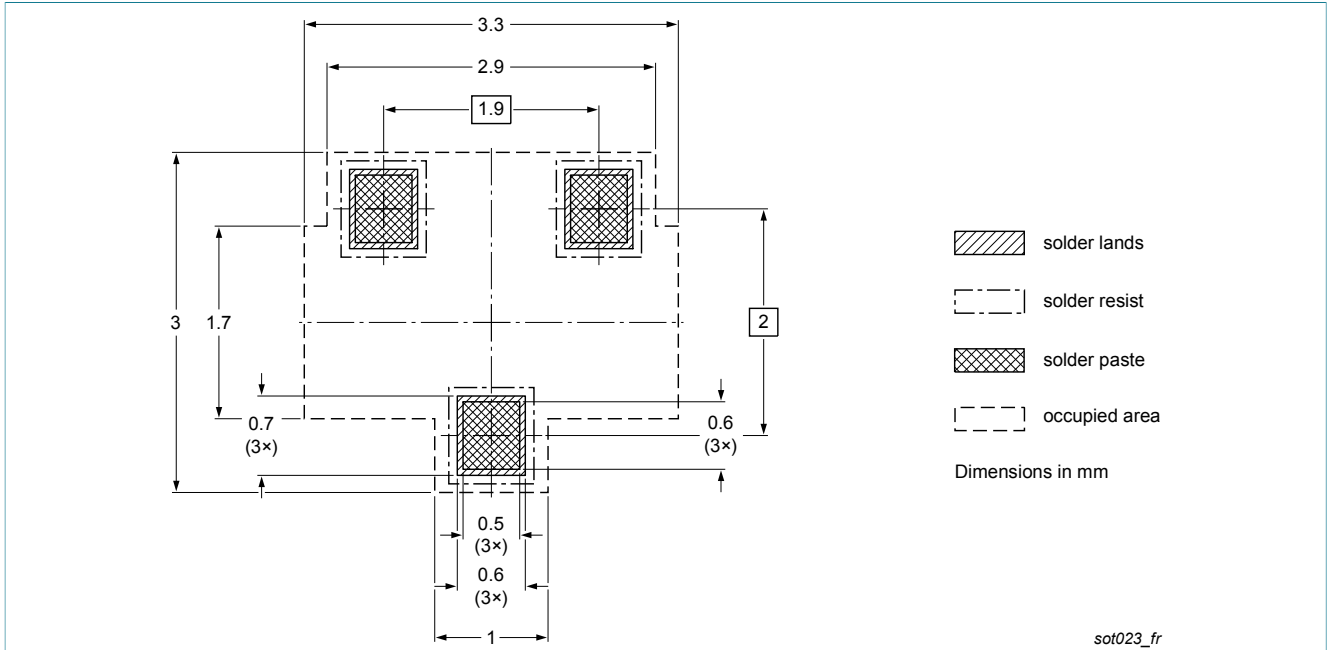
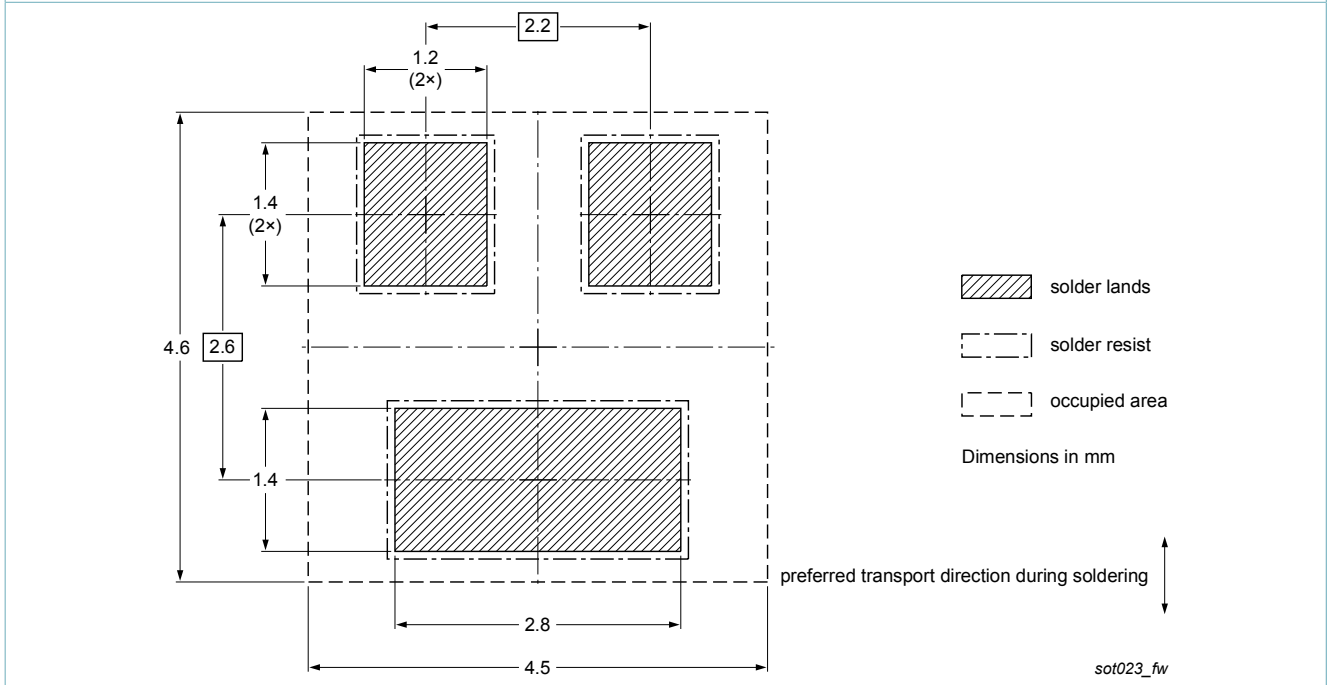


Fig. 18. Package outline TO-236AB (SOT23)

### 13. Soldering



**Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)**



**Fig. 20. Wave soldering footprint for TO-236AB (SOT23)**

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BSH111BK v.1	20141126	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Date of release: 26 November 2014